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강의계획서

| 검색조건 : | |
|--------------------------|----|
| 교양/교직/군사학 | ▼ |
| 첨성인기초 - 독서와토론 | ▼ |
| [수업시간][건물 및 교과구분 코드][검색] | 조회 |

[영문강의계획서보기(Syllabus)]

| 과목명 | 반도체소자특성 |
|------------|---|
| 과목번호 | ELEC785001 |
| 학점 | 3.0 |
| 개설대학 | 전자공학부 |
| 개설학기 | 20181 |
| 교과구분 | 전공 |
| 담당교수 | 박홍식 |
| 강의시간 | 월5B6A6B 월7A7B8A |
| 강의실명 | IT대학3호관(공대11호관)104 IT대학3호관(공대11호관)104 |
| 연락처/E-mail | ** 통합정보시스템 로그인- 수업/성적- 수업- "강의담당교수조회"에서 확인 가능함. |
| 면담시간 | |
| 강의언어 | 한국어 |

[강의계획서]

강의개요 및 목적

Understanding the operation and characterization of electrical and optical semiconductor devices (mordern field-effect tr ansistors, memory devices, photodetectors, oprical modulators, solar cells) and their practical applications.

교재 및 참고문헌

- 0. Class notes and lecture slides selected and combined from following references.
- 1. Yuan Taur, Fundamentals of Modern VLSI Devices (2nd Ed)
- 2. S Sze, Physics of Semiconductor Devices (3rd Ed)
- 4. D. K. Schroder, Semiconductor Material and Device Characterization (2nd Ed)

Most topics will be covered by the class notes/slides and textbooks, but some of the topics may go beyond (or beside) the textbook: handouts and references will be provided when necessary

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| 강의진행 방법 및 활용매체 | |
| | |
| Lecture slides and notes | |
| | |
| 과제, 평가방법, 선수과목 | |
| | |
| Midterm exam: 40% | |
| Final exam: 40% | |
| Attendance and homework: 20% | |
| | |
| 수강에 특별히 참고할 사항 | |
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| 장애학생을 위한 학습지원 사항 | |
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| Necessary aids will be offered for students with disabilities. | |
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[강의 내용 및 일정]

| | [강의 내용 및 일정] | | | |
|----|---|-----------|-----------|----|
| no | 강의 요목 및 수업목표 | 과제 및 연구문제 | 교재 및 참고자료 | 비고 |
| 1 | Class overview Review of semiconducting material parameters Review of semiconductor device parameters | | | |
| 2 | Review of semicoductor physics Drawing and understanding band diagrams | | | |
| 3 | Metal-semiconductor junctions and characterization Semiconductor-semiconductor junctions and characterization | | | |
| 4 | Metal-oxide-semiconductor junctions | | | |
| 5 | Field-effect transistors (1) | | | |
| 6 | Field-effect transistors (2) | | | |
| 7 | CMOS technology | | | |
| 8 | In-class midterm exam | | | |
| 9 | CMOS performance factors and scaling issues | | | |
| 10 | Review of memory device technology Volatile memory devices | | | |
| 11 | Nonvolatile memory devices | | | |
| 12 | Nano devices based on low-dimensional materials such as graphene and CNT | | | |
| 13 | Optical devices: photodetectors | | | |
| 14 | Optical devices: solar cells, semiconductor optical modulators | | | |

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| 15 | In-class final exam | | |
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수험부정행위시, 경북대학교 수험부정행위에관한처벌규정에 의거 그 정상에 따라 수험자격박탈, 근신, 유기·무기정학, 또는 제적 처분될 수 있으니, 각별히 유의하여 주시기 바람.

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